

# Complementary Silicon Plastic Power Transistors

... designed for use in general purpose amplifier and switching applications.

- Collector–Emitter Saturation Voltage —  
 $V_{CE} = 1.2 \text{ Vdc (Max) @ } I_C = 3.0 \text{ Adc}$
- Collector–Emitter Sustaining Voltage —  
 $V_{CEO(sus)} = 80 \text{ Vdc (Min.) BD241B, BD242B}$   
 $= 100 \text{ Vdc (Min.) BD241C, BD242C}$
- High Current Gain — Bandwidth Product  
 $f_T = 3.0 \text{ MHz (Min) @ } I_C = 500 \text{ mAdc}$
- Compact TO–220 AB Package

## MAXIMUM RATINGS

Rating	Symbol	BD241B BD242B	BD241C BD242C	Unit
Collector–Emitter Voltage	$V_{CEO}$	80	100	Vdc
Collector–Emitter Voltage	$V_{CES}$	90	115	Vdc
Emitter–Base Voltage	$V_{EB}$	5.0		Vdc
Collector Current — Continuous Peak	$I_C$	3.0 5.0		Adc Adc
Base Current	$I_B$	1.0		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	40 0.32		Watts $\text{W}/^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–65 to +150		$^\circ\text{C}$

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.125	$^\circ\text{C}/\text{W}$

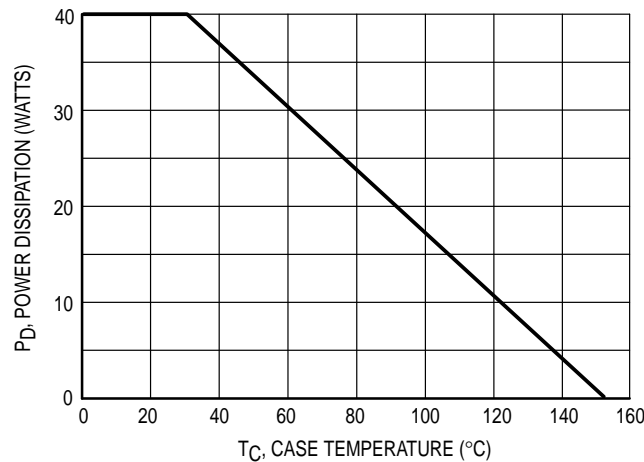


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 7

**NPN**  
**BD241B**  
  
**BD241C\***  
**PNP**  
**BD242B**  
  
**BD242C\***

\*Motorola Preferred Device

**3 AMPERE**  
**POWER TRANSISTORS**  
**COMPLEMENTARY**  
**SILICON**  
**80, 100 VOLTS**  
**40 WATTS**

**CASE 221A–06**  
**TO–220AB**

# BD241B BD241C BD242B BD242C

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage <sup>1</sup> ( $I_C = 30\text{ mAdc}$ , $I_B = 0$ )	$V_{CEO}$	80 100		Vdc
Collector Cutoff Current ( $V_{CE} = 60\text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$		0.3	mAdc
Collector Cutoff Current ( $V_{CE} = 80\text{ Vdc}$ , $V_{EB} = 0$ ) ( $V_{CE} = 100\text{ Vdc}$ , $V_{EB} = 0$ )	$I_{CES}$		200 200	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{BE} = 5.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$		1.0	mAdc

## ON CHARACTERISTICS<sup>1</sup>

DC Current Gain ( $I_C = 1.0\text{ Adc}$ , $V_{CE} = 4.0\text{ Vdc}$ ) ( $I_C = 3.0\text{ Adc}$ , $V_{CE} = 4.0\text{ Vdc}$ )	$h_{FE}$	25 10		
Collector–Emitter Saturation Voltage ( $I_C = 3.0\text{ Adc}$ , $I_B = 600\text{ Adc}$ )	$V_{CE(\text{sat})}$		1.2	Vdc
Base–Emitter On Voltage ( $I_C = 3.0\text{ Adc}$ , $V_{CE} = 4.0\text{ Vdc}$ )	$V_{BE(\text{on})}$		1.8	Vdc

## DYNAMIC CHARACTERISTICS

Current Gain – Bandwidth Product <sup>2</sup> ( $I_C = 500\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f_{\text{test}} = 1\text{ MHz}$ )	$f_T$	3.0		MHz
Small–Signal Current Gain ( $I_C = 0.5\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1\text{ kHz}$ )	$h_{fe}$	20		

<sup>1</sup> Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

<sup>2</sup>  $f_T = |h_{fe}| \cdot f_{\text{test}}$ .

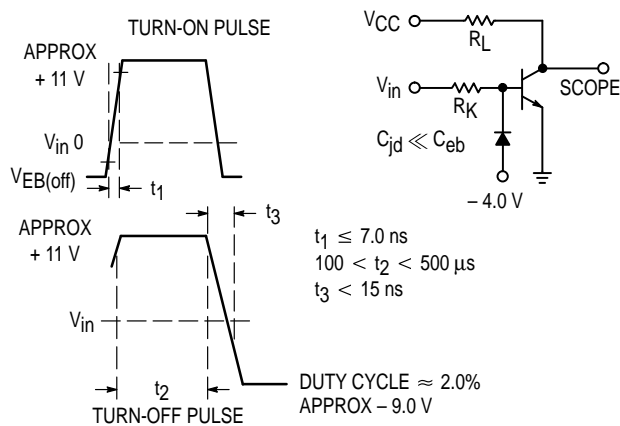


Figure 2. Switching Time Equivalent Circuit

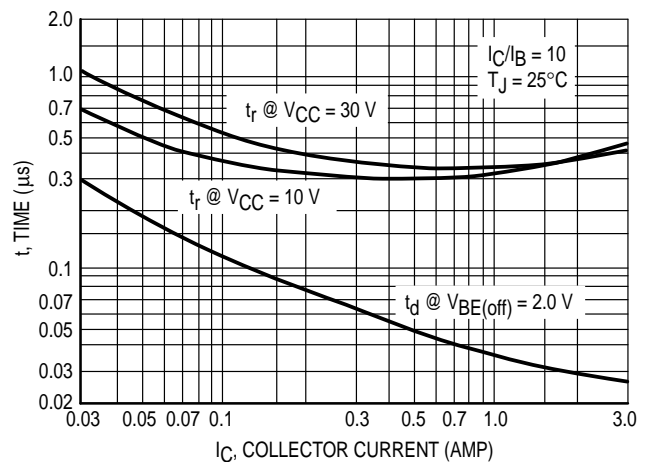


Figure 3. Turn–On Time

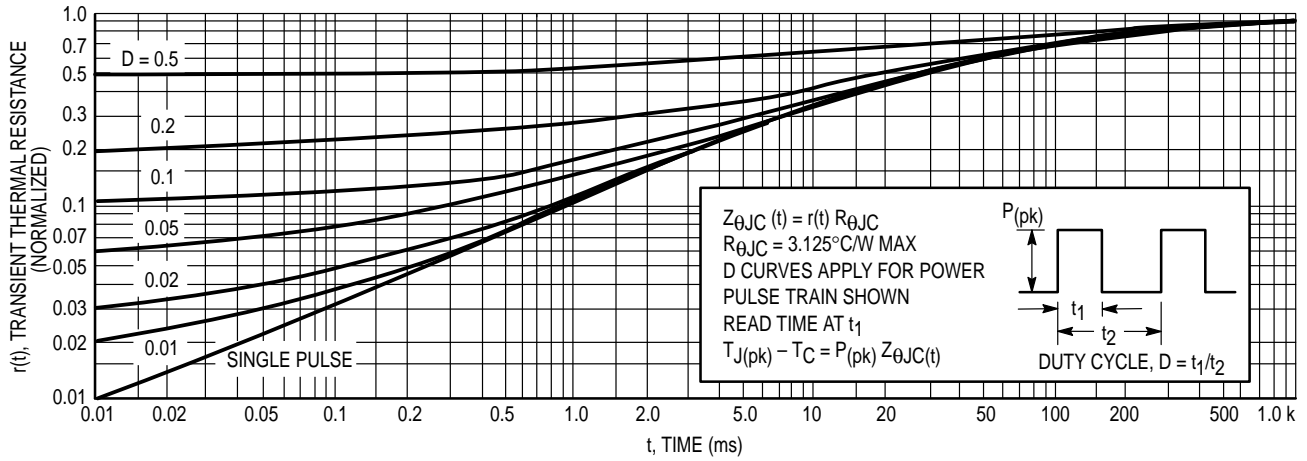


Figure 4. Thermal Response

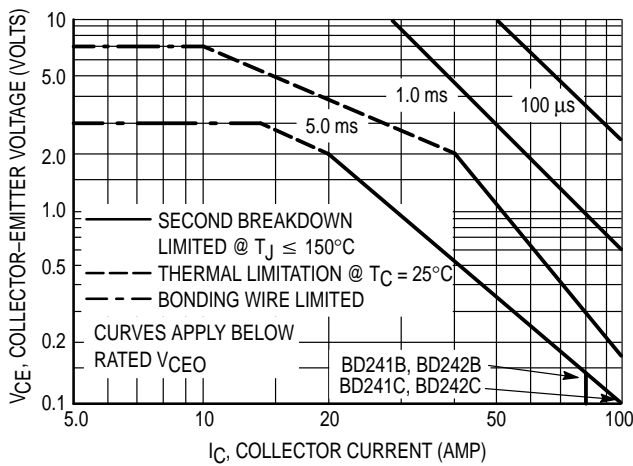


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ}\text{C}$ ,  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

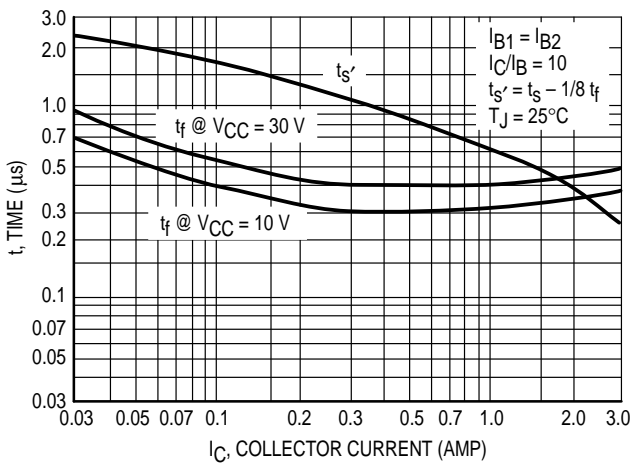


Figure 6. Turn-Off Time

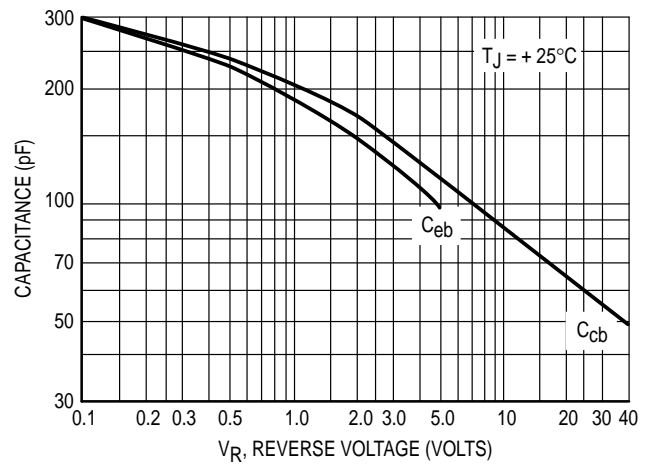
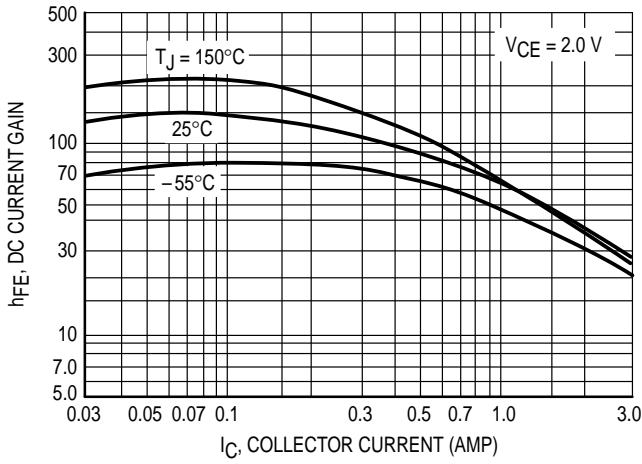
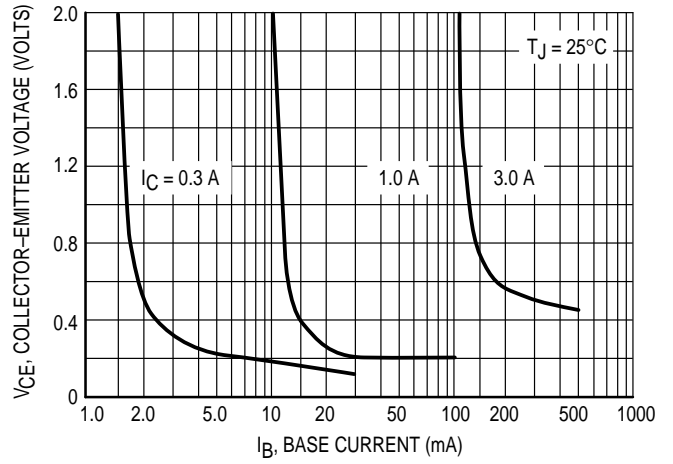


Figure 7. Capacitance

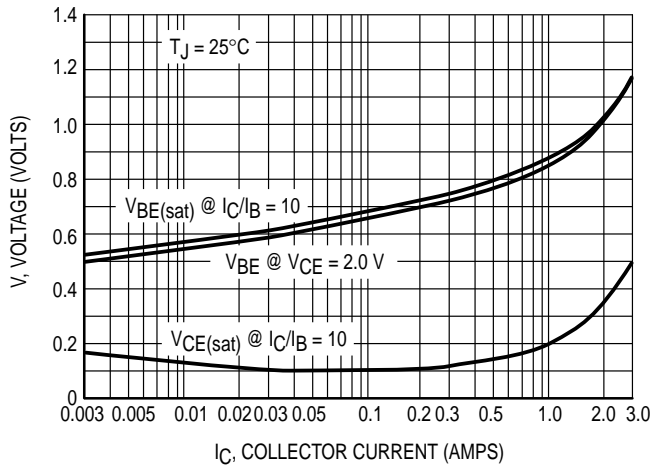
**BD241B BD241C BD242B BD242C**



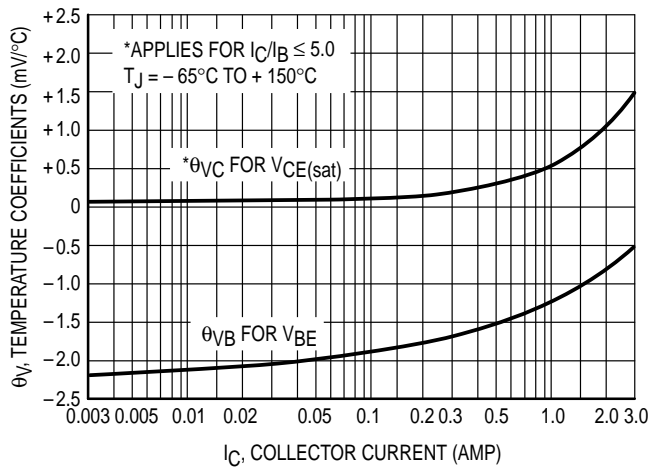
**Figure 8. DC Current Gain**



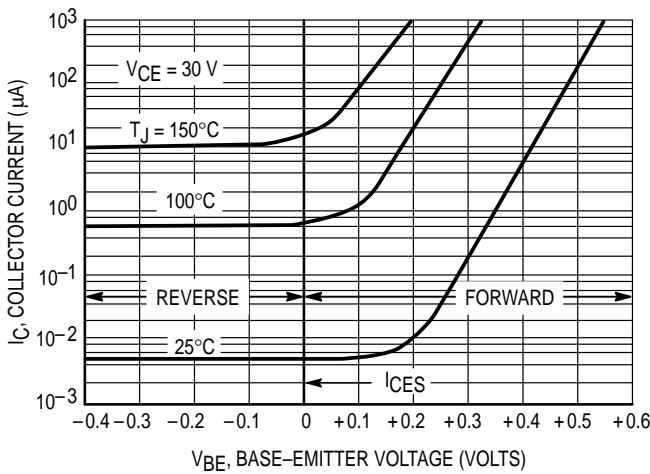
**Figure 9. Collector Saturation Region**



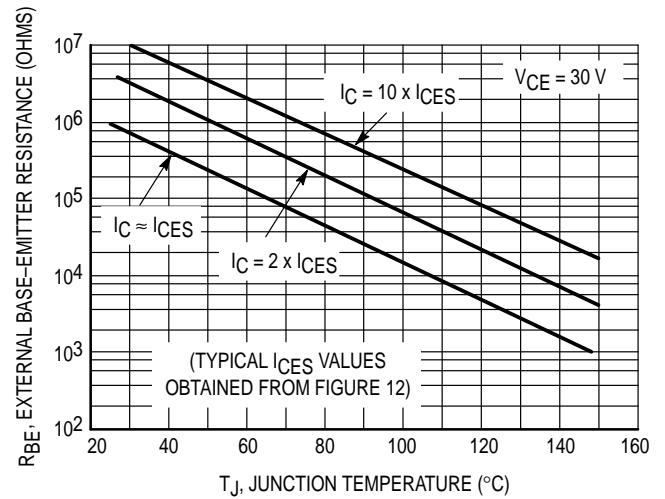
**Figure 10. "On" Voltages**



**Figure 11. Temperature Coefficients**



**Figure 12. Collector Cut-Off Region**



**Figure 13. Effects of Base-Emitter Resistance**

PACKAGE DIMENSIONS




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

- STYLE 1:
- PIN 1. BASE
  2. COLLECTOR
  3. EMITTER
  4. COLLECTOR

CASE 221A-06  
TO-220AB  
ISSUE Y

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**How to reach us:**

**USA / EUROPE:** Motorola Literature Distribution;  
P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

**JAPAN:** Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki,  
6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

**MFAX:** RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609  
**INTERNET:** <http://Design-NET.com>

**HONG KONG:** Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,  
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

